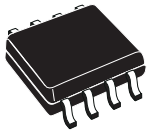
STS4DNFS30L

N-channel 30V - 0.044Ω - 4A SO-8
STripFET™ MOSFET plus SCHOTTKY rectifier

General features

MOSFET	V_{DSS}	$R_{DS(on)}$	I_D
	30V	<0.056Ω	4A
SCHOTTKY	$I_{F(AV)}$	V_{RRM}	$V_{F(MAX)}$
	3A	30V	0.51V



S0-8

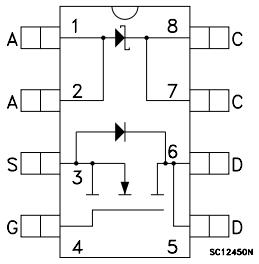
Description

This product associates the latest low voltage STripFET™ in n-channel version to a low drop Schottky diode. Such configuration is extremely versatile in implementing, a large variety of DC-DC converters for printers, portable equipment, and cellular phones.

Applications

- Switching application

Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STS4DNFS30L	S4DNFS30L	SO-8	Tape & reel

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (v_{gs} = 0)	30	V
V_{DGR}	Drain-gate voltage (R_{GS} = 20 kΩ)	30	V
V_{GS}	Gate- source voltage	±16	V
I_D	Drain current (continuous) at T_C = 25°C	4	A
I_D	Drain current (continuous) at T_C = 100°C	2.5	A
I_{DM} (1)	Drain current (pulsed)	16	A
P_{TOT}	Total dissipation at T_C = 25°C dual operation	2	W

1. Pulse width limited by safe operating area

Table 2. Schottky absolute maximum ratings

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		30	V
$I_{F(RMS)}$	RMS forward current		20	A
$I_{F(AV)}$	Average forward current	TL=125°C δ=0.5	3	A
I_{FSM}	Surge non repetitive forward current	tp = 10 ms Sinusoidal	75	A
I_{RRM}	Repetitive peak reverse current	tp = 2 µs F=1 kHz	1	A
I_{RSM}	Non repetitive peak reverse current	tp = 100 µs	1	A
dv/dt	Critical rate of rise of reverse voltage		10000	V/µs

Table 3. Thermal data

R_{thj-a}	Thermal resistance junction-ambient MOSFET(1)	62.5	°C/W °C/W
T_J	Junction temperature	-55 to 150	°C
T_{stg}	Storage temperature range	-55 to 150	°C

1. Mounted on FR-4 board (steady state)

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	I_D = 250 µA, V_{GS} = 0	30			V
I_{DSS}	Zero gate voltage Drain current (V_{GS} = 0)	V_{DS} = Max rating			1	µA
		V_{DS}=Max rating, T_C=125°C			10	µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ±16V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250µA	1			V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10V, I_D = 2A		0.044	0.055	Ω
		V_{GS} = 5V, I_D = 2A		0.051	0.065	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS}= 15V, I_D=2A		5		S
C_{iss}	Input capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		330		pF
C_{oss}	Output capacitance			90		pF
C_{rss}	Reverse transfer capacitance			40		pF
Q_g	Total gate charge	V_{DD} = 24V, I_D = 4A, V_{GS} = 5V		6.5	9	nC
Q_{gs}	Gate-source charge			3.6		nC
Q_{gd}	Gate-drain charge			2		nC

1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5.

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD}=15 V, I_D=2A, R_G=4.7Ω, V_{GS}=5V (see Figure 12)		11		ns
t_r	Rise time			100		ns
$t_{d(off)}$	Turn-off delay time	V_{DD}=15 V, I_D=2A, R_G=4.7Ω, V_{GS}=5V (see Figure 12)		25		ns
t_f	Fall time			22		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				4	A
I_{SDM} (1)	Source-drain current (pulsed)				16	A
V_{SD} (2)	Forward on voltage	I_{SD} = 4A, V_{GS} = 0			1.2	V
t_{rr}	Reverse recovery time	I_{SD} = 4A, V_{DD} = 15V di/dt = 100A/µs, T_j = 150°C (see Figure 14)		35		ns
Q_{rr}	Reverse recovery charge			25		nC
I_{RRM}	Reverse recovery current			1.4		A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

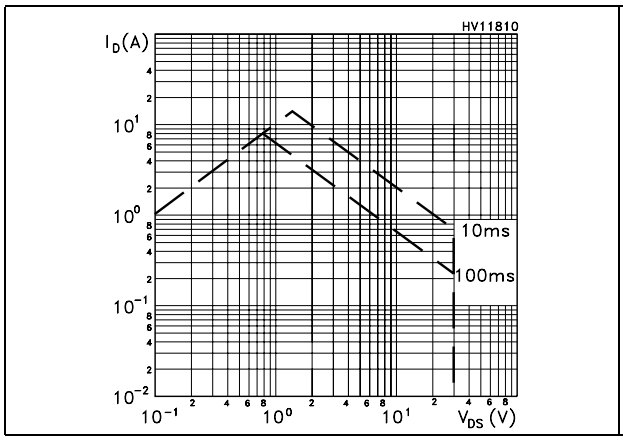


Figure 2. Thermal impedance

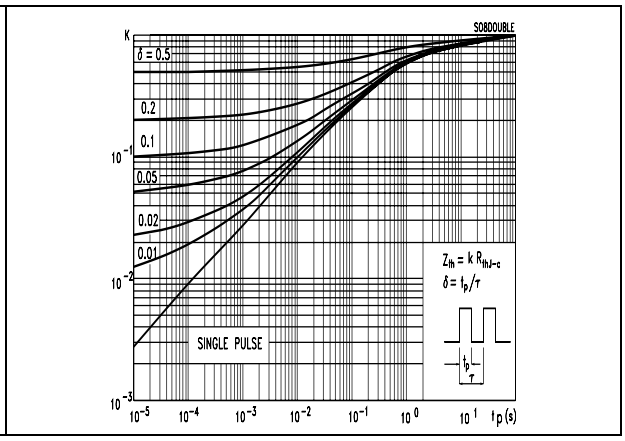


Figure 3. Output characteristics

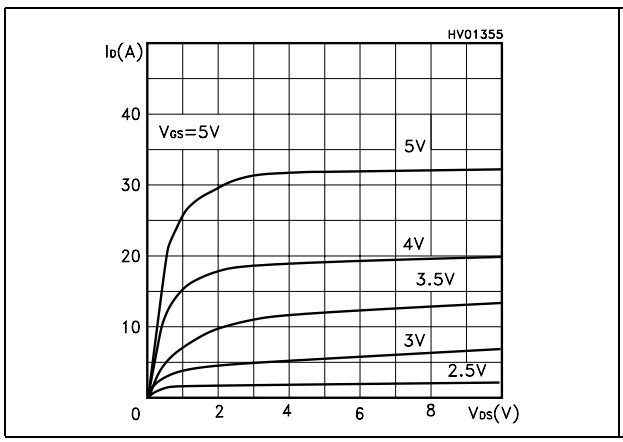


Figure 4. Transfer characteristics

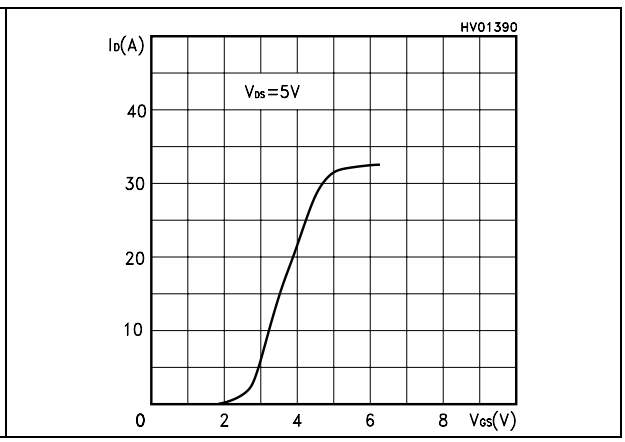


Figure 5. Transconductance

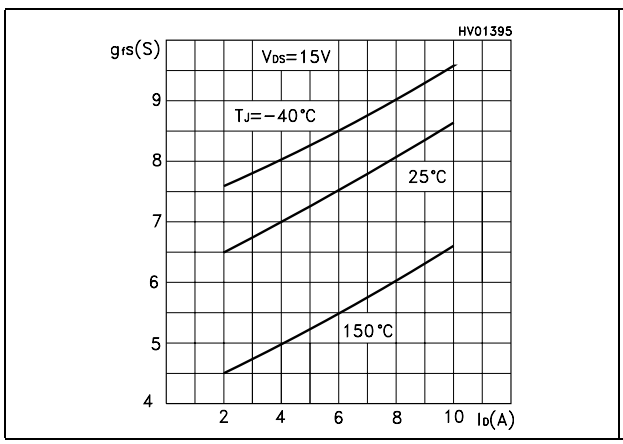


Figure 6. Static drain-source on resistance

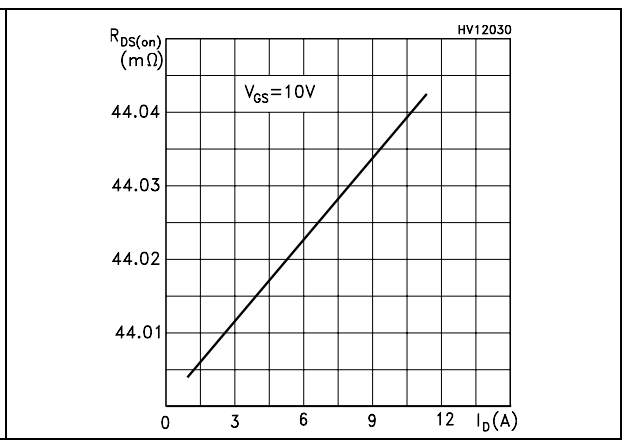


Figure 7. Gate charge vs. gate-source voltage

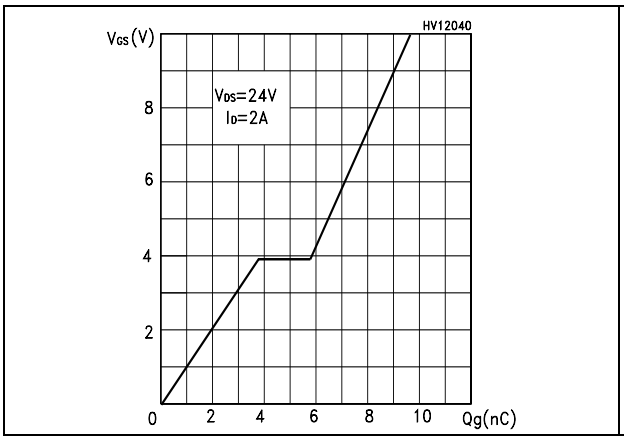


Figure 8. Capacitance variations

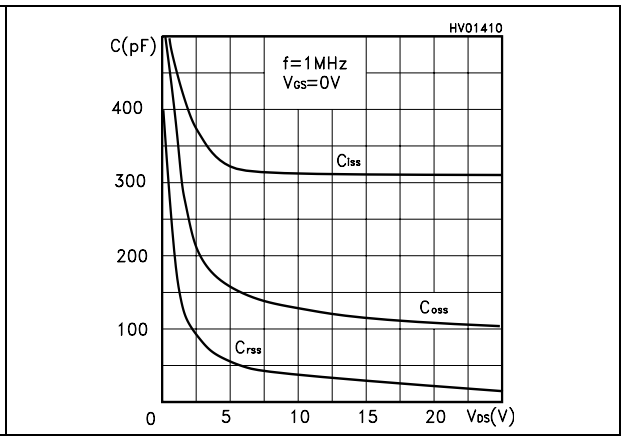


Figure 9. Normalized gate threshold voltage vs. temperature

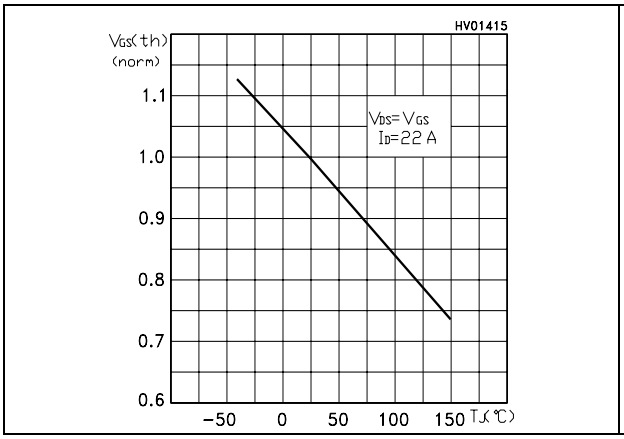


Figure 10. Normalized on resistance vs. temperature

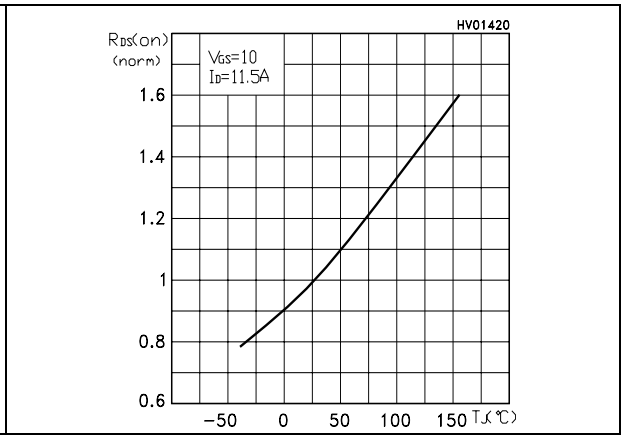
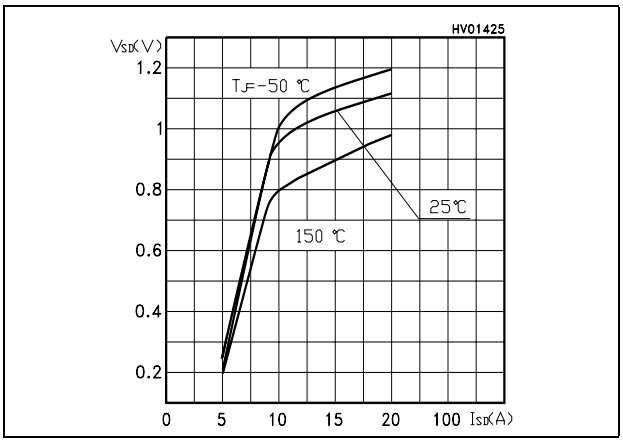


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load

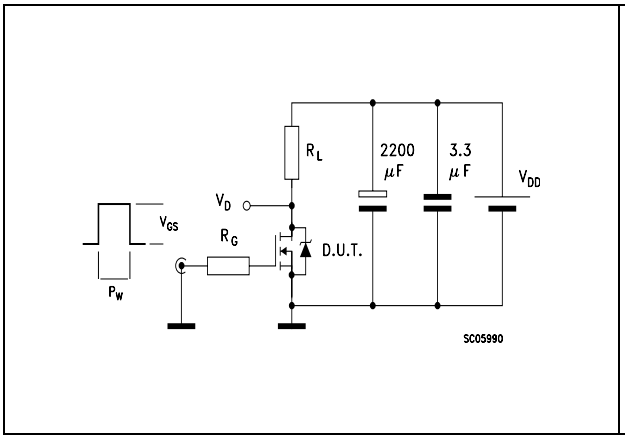


Figure 13. Gate charge test circuit

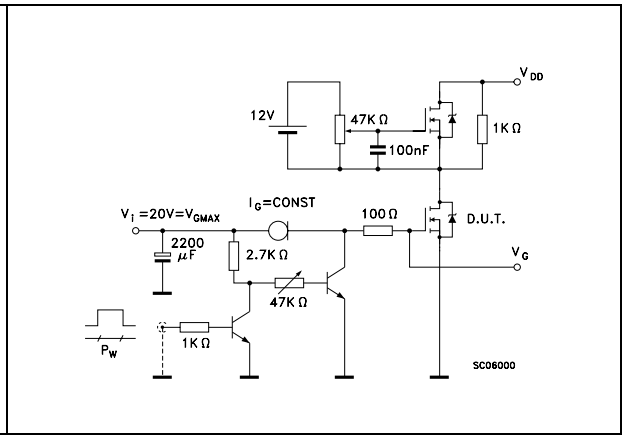


Figure 14. Test circuit for inductive load switching and diode recovery times

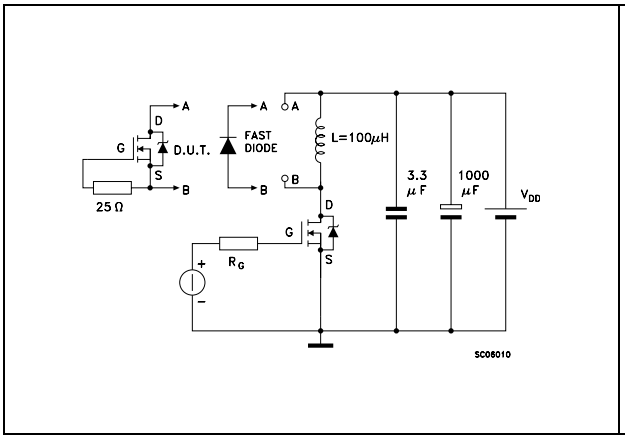


Figure 15. Unclamped Inductive load test circuit

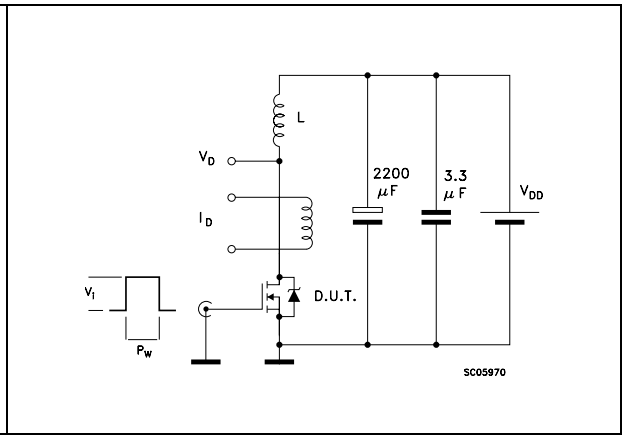


Figure 16. Unclamped inductive waveform

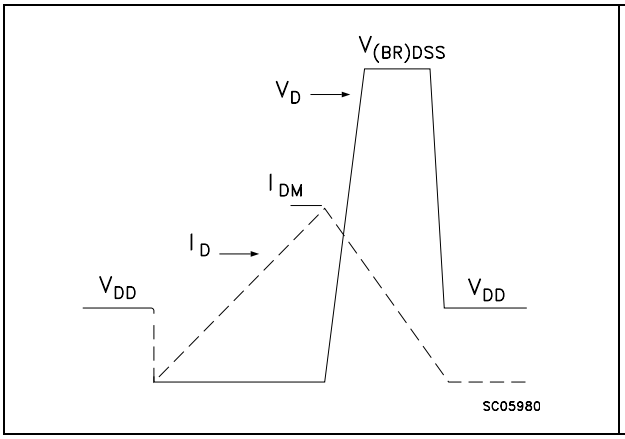
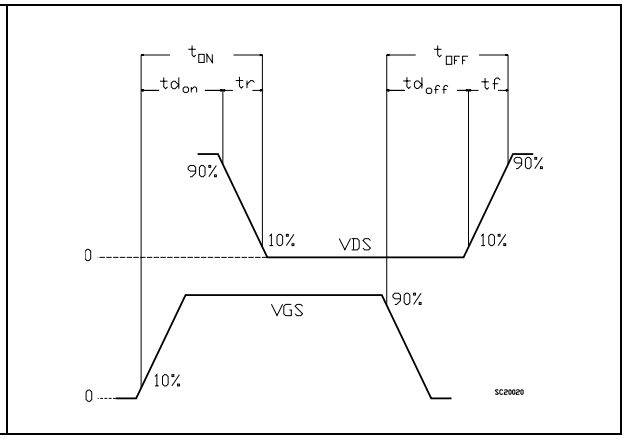


Figure 17. Switching time waveform

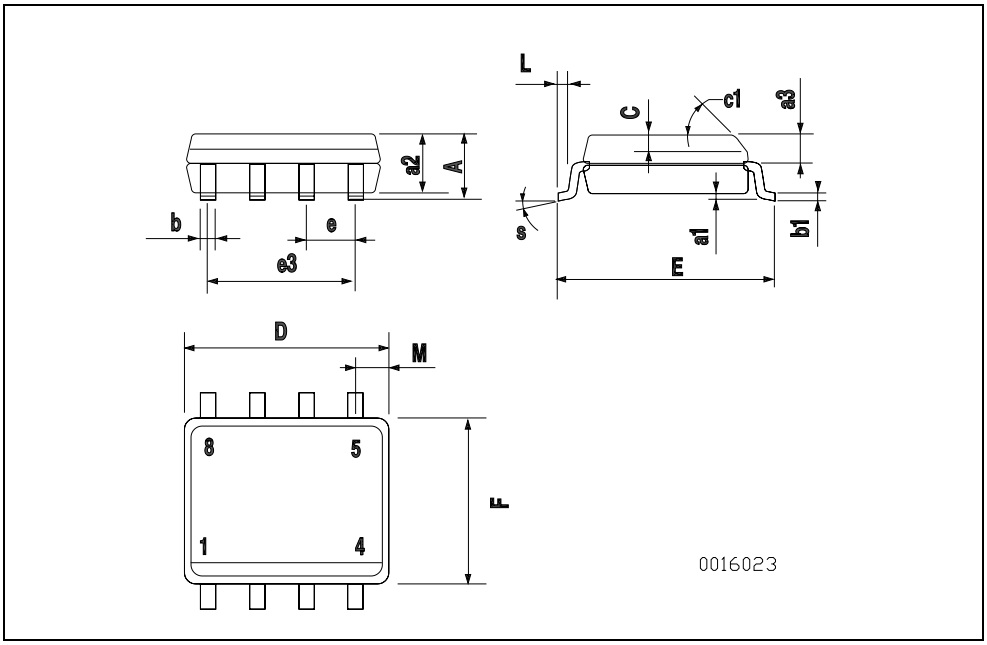


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at : *www.st.com*

SO-8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



5 Revision history

Table 8. Revision history

Date	Revision	Changes
21-Jun-2004	2	Complete version
10-Nov-2006	3	The document has been reformatted
26-Jan-2007	4	Typo mistakes on *Table 1*.

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